

SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

CDBS0130

I_o = 100mA

V_R = 30 Volts



Features

Designed for mounting on small surface.

Extremely thin package.

Low stored charge.

Majority carrier conduction.

Mechanical data

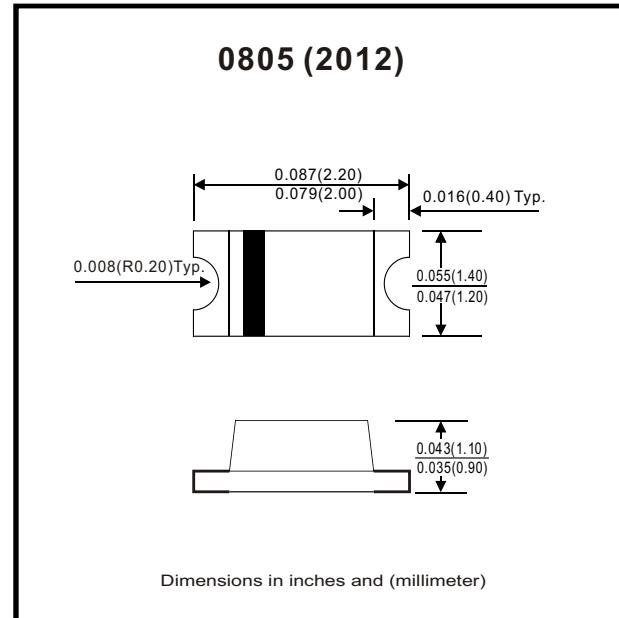
Case: 0805(2012) standard package,
molded plastic.

Terminals: Gold plated, solderable per
MIL-STD-750, method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.0048 gram(approx.).



Maximum Rating (at TA=25°C unless otherwise noted)

| Parameter | Conditions | Symbol | Min | Typ | Max | Unit |
|---------------------------------|--|------------------|-----|------|------|------|
| Repetitive peak reverse voltage | | V _{RRM} | | | 35 | V |
| Reverse voltage | | V _R | | | 30 | V |
| Average forward current | | I _o | | | 100 | mA |
| Forward current,surge peak | 8.3 ms single half sine-wave superimposed on rate load(JEDEC method) | I _{FSM} | | 1000 | | mA |
| Power Dissipation | | P _D | | | 250 | mW |
| Sunction temperature | | T _{TSG} | -40 | | +125 | °C |
| Junction temperature | | T _j | | | +125 | °C |

Electrical Characteristics (at TA=25°C unless otherwise noted)

| Parameter | Conditions | Symbol | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------------|----------------|-----|-----|------|------|
| Forward voltage | I _F = 100 mA DC | V _F | | | 0.44 | V |
| Reverse current | V _R = 30V | I _R | | | 30 | uA |
| Capacitance between terminals | F = 1 MHZ and 10 VDC reverse voltage | C _T | | 10 | | pF |

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RATING AND CHARACTERISTIC CURVES (CDBS0130)

Fig. 1 - Forward characteristics

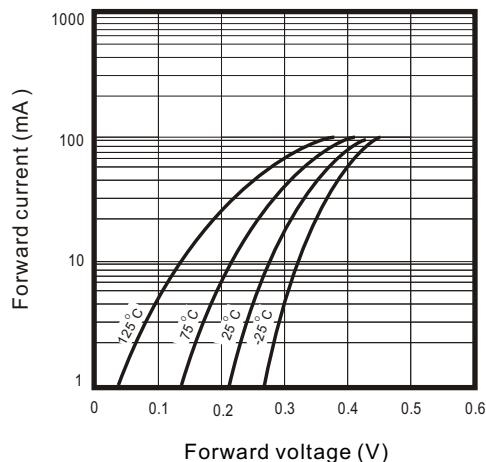


Fig. 2 - Reverse characteristics

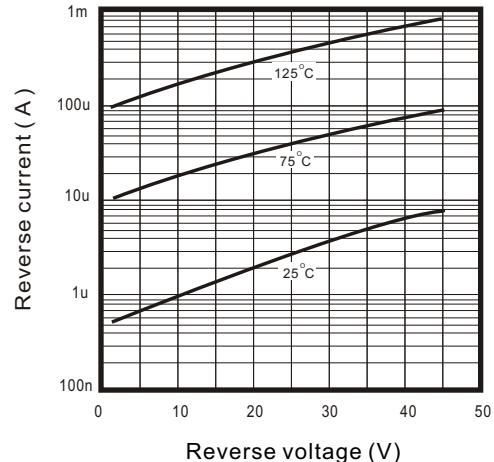


Fig.3 - Capacitance between terminals characteristics

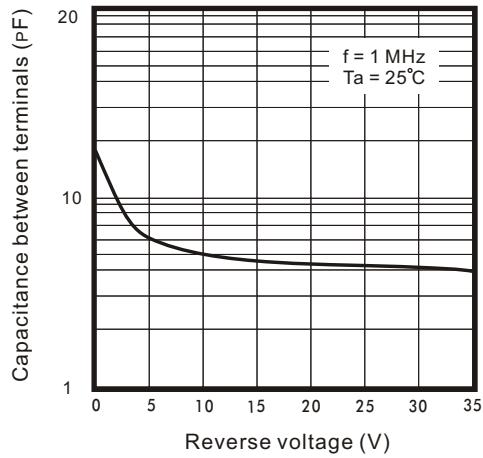


Fig.4 - Current derating curve

